

Marked up copy of claims as amended:

IN THE CLAIMS:

Please amend the claims as follows:

42.(Amended) The semiconductor device according to claim 12, wherein said [tungsten film] gate electrode has an electrical resistivity of $20\ \mu\Omega\cdot\text{cm}$ or less.

45.(Amended) The semiconductor device according to claim 43, wherein said [tungsten film] gate electrode has an electrical resistivity of $20\ \mu\Omega\cdot\text{cm}$ or less.

51.(Amended) The semiconductor device according to claim 49, wherein said [tungsten film] gate electrode has an electrical resistivity of $20\ \mu\Omega\cdot\text{cm}$ or less.

57.(Amended) The semiconductor device according to claim 55, wherein said [tungsten film] gate electrode has an electrical resistivity of $20\ \mu\Omega\cdot\text{cm}$ or less.

63.(Amended) The semiconductor device according to claim 61, wherein said [tungsten film] gate electrode has an electrical resistivity of $20\ \mu\Omega\cdot\text{cm}$ or less.

69.(Amended) The semiconductor device according to claim 67, wherein said [tungsten film] gate electrode has an electrical resistivity of $20\ \mu\Omega\cdot\text{cm}$ or less.

75.(Amended) The semiconductor device according to claim 73, wherein said [tungsten film] gate electrode has an electrical resistivity of $20\ \mu\Omega\cdot\text{cm}$ or less.

Please add the following new claims:

79.(New) A semiconductor device comprising:

a semiconductor layer over a substrate; and

a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said gate electrode comprises a first conductive layer comprising nitride and a second conductive layer comprising tungsten on said first conductive layer, and wherein at least said first conductive layer has a tapered cross section.

80.(New) The semiconductor device according to claim 79, wherein said gate electrode is located over said semiconductor layer.

81.(New) The semiconductor device according to claim 79, wherein said gate electrode has an electrical resistivity of $20\ \mu\Omega\cdot\text{cm}$ or less.

82.(New) The semiconductor device according to claim 79, wherein said semiconductor device is an active matrix type liquid crystal display device.

83.(New) The semiconductor device according to claim 79, wherein said semiconductor device is an EL display device.

84.(New) The semiconductor device according to claim 79, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a

projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, and a portable information terminal.

85.(New) A semiconductor device comprising:

a semiconductor layer over a substrate; and

a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said gate electrode comprises a first conductive layer comprising tungsten nitride and a second conductive layer comprising tungsten on said first conductive layer, and wherein at least said first conductive layer has a tapered cross section.

86.(New) The semiconductor device according to claim 85, wherein said gate electrode is located over said semiconductor layer.

87.(New) The semiconductor device according to claim 85, wherein said gate electrode has an electrical resistivity of $20 \mu\Omega\cdot\text{cm}$ or less.

88.(New) The semiconductor device according to claim 85, wherein said semiconductor device is an active matrix type liquid crystal display device.

89.(New) The semiconductor device according to claim 85, wherein said semiconductor device is an EL display device.

90.(New) The semiconductor device according to claim 85, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, and a portable information terminal.

91.(New) A semiconductor device comprising:
a semiconductor layer over a substrate; and
a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said gate electrode comprises a first conductive layer comprising nitride and a second conductive layer comprising tungsten on said first conductive layer, and wherein said second conductive layer has a thickness between 200 and 400 nm.

92.(New) The semiconductor device according to claim 91, wherein said gate electrode is located over said semiconductor layer.

93.(New) The semiconductor device according to claim 91, wherein said gate electrode has an electrical resistivity of $20 \mu\Omega\cdot\text{cm}$ or less.

94.(New) The semiconductor device according to claim 91, wherein said semiconductor device is an active matrix type liquid crystal display device.

95.(New) The semiconductor device according to claim 91, wherein said semiconductor device is an EL display device.

96.(New) The semiconductor device according to claim 91, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, and a portable information terminal.

97.(New) A semiconductor device comprising:

a semiconductor layer over a substrate; and

a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween,

wherein said gate electrode comprises a first conductive layer comprising tungsten nitride and a second conductive layer comprising tungsten on said first conductive layer, and wherein said second conductive layer has a thickness between 200 and 400 nm.

98.(New) The semiconductor device according to claim 97, wherein said gate electrode is located over said semiconductor layer.

99.(New) The semiconductor device according to claim 97, wherein said gate electrode has an electrical resistivity of $20 \mu\Omega\cdot\text{cm}$ or less.

100.(New) The semiconductor device according to claim 97, wherein said semiconductor device is an active matrix type liquid crystal display device.

101.(New) The semiconductor device according to claim 97, wherein said semiconductor device is an EL display device.

102.(New) The semiconductor device according to claim 97, wherein said semiconductor device is at least one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a mobile computer, a personal computer, and a portable information terminal.